

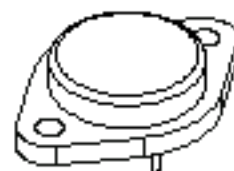
# PNP Transistor

## 2N6329 (#23928)

### Package

Division Lawrence  
Mil-Spec (none)  
Shipping (none)

Qual Data (none)



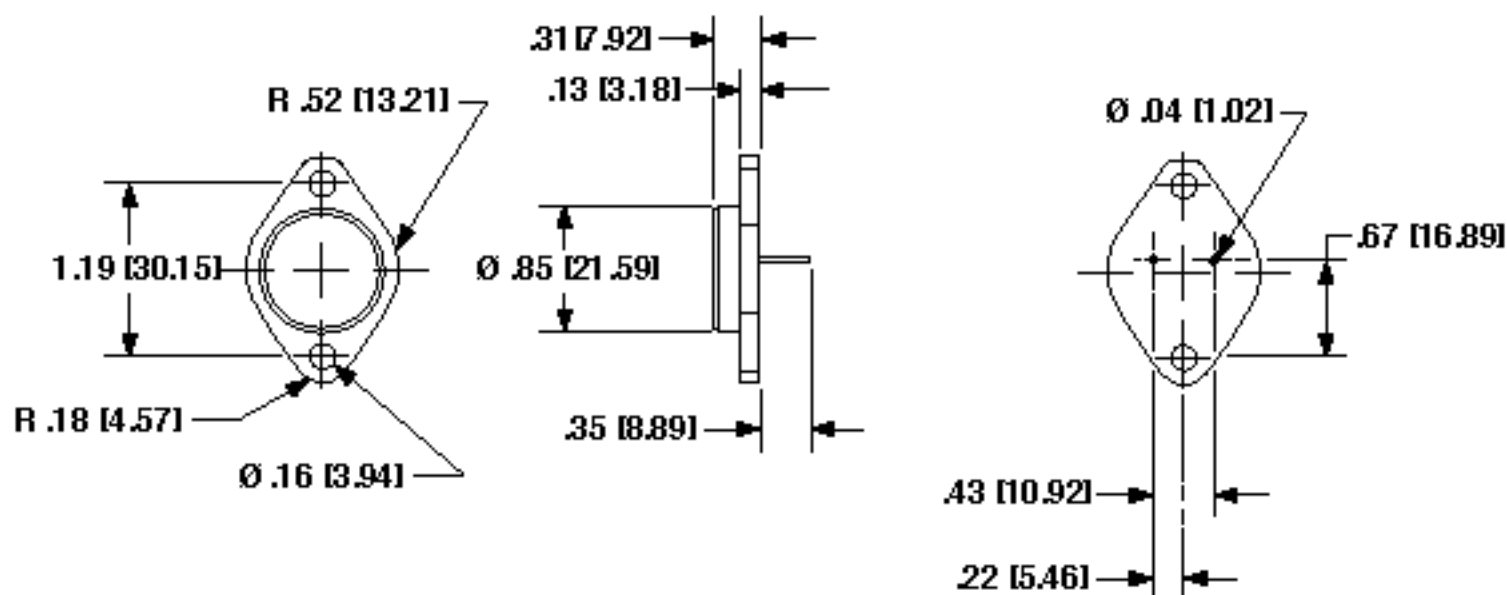
TO-3

Absolute Maximum Ratings	Symbol	Max	Unit
Power Dissipation	Power	200	W
Collector Current	$I_C$	30	A
Breakdown Voltage Collector-to-Base	$B_{V(CBO)}$	60	V
Voltage Collector to Emitter Open	$V_{CEO}$	60	V
Voltage Emitter to Base Open	$BV_{EBO}$	5	V

Electrical Characteristics	Symbol	Min	Typ	Max	Unit
Collector Emitter Saturation Voltage					
( $I_B=1.5$ mA, $I_C=30$ mA, $T_A=25$ °C, 300µs pulse)	$V_{CE(sat)}$			1.5	V
DC Current Gain					
( $I_C=30$ mA, $T_A=25$ °C, 300µs pulse)	HFE	6		30	

TO-3

Microsemi



ALL DIMENSIONS SHOWN  
ARE TYPICAL VALUES

NOTE: DIMENSIONS IN INCHES [MM]

THIS DRAWING IS FOR REFERENCE ONLY. PLEASE REFER TO THE MICROSEMI PUBLISHED DATA SHEET.